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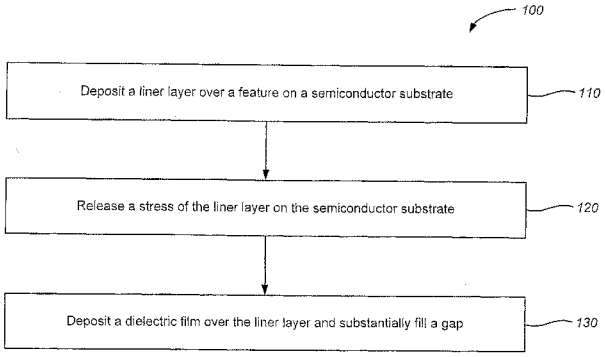


FIG. 1

(57) Abstract: A deposition method for releasing a stress buildup of a feature over a semiconductor substrate with dielectric material is provided. The feature includes lines separated by a gap. The method includes forming a liner layer over the feature on the semiconductor substrate in a chamber. A stress of the liner layer over the feature is released to substantially reduce bending of the lines of the feature. A dielectric film is deposited over the stress-released liner layer to substantially fill the gap of the feature.

WO 2010/011476 A4